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O-doped Sb materials for improved thermal stability and high-speed phase change memory application

Yifeng Hu,^{1,a)} Xiaoqin Zhu,^{1, b)} Hua Zou,¹ Long Zheng,¹ Sannian Song² and Zhitang Song²

¹School of Mathematics and Physics, Jiangsu University of Technology, Changzhou 213001, China

²State Key Laboratory of Functional Materials for Informatics, Shanghai Institute of Micro-System and Information Technology, Chinese Academy of Sciences, Shanghai 200050, China

Abstract The O-doped Sb materials were proved to have higher crystallization temperature ($\sim 205^{\circ}\text{C}$), larger crystallization activation energy (3.95 eV) and better data retention ability (143°C for 10 years). The band gap was broadened by O-doping and the grain size was refined. The formation of Sb oxide increased the binding energy. The fast phase change speed was obtained for O-doped Sb materials by picosecond laser technology. After O-doping, the phase change film had a smaller surface roughness (1.05 nm).

Keywords: Sb material, oxygen-doping, thermal stability, high-speed

^{a)}Corresponding author.

E-mail address: hyf@jsut.edu.cn

^{b)}Corresponding author.

E-mail address: pcram@jsut.edu.cn

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